

P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 40	0.012 at V _{GS} = - 10 V	- 60 ^d	60
	0.018 at V _{GS} = - 4.5 V	- 48 ^d	

FEATURES

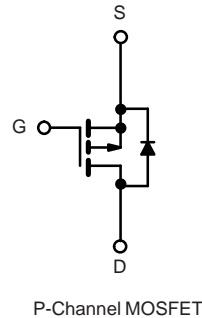
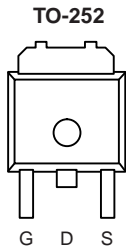
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT

APPLICATIONS

- Power Switch
- Load Switch in High Current Applications
- DC/DC Converters



ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 40	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 60 ^d	A
		T _C = 70 °C	- 60 ^d	
Pulsed Drain Current	I _{DM}	- 180		
Avalanche Current	I _{AS}	- 46		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	106	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	73.5 ^b	W
	T _A = 25 °C ^c		2.5	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W
Junction-to-Case (Drain)	R _{thJC}	1.7	

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).
- Package limited.

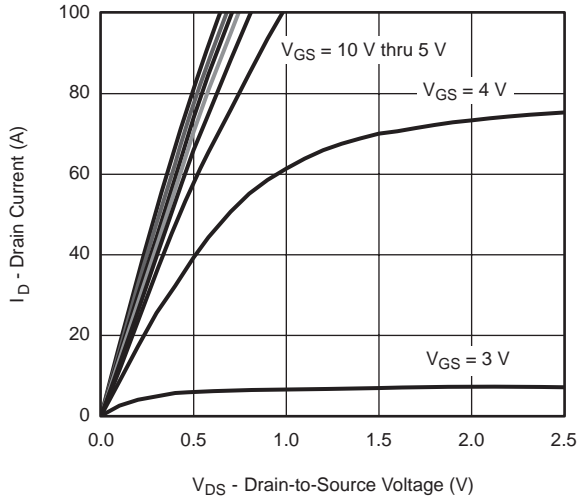
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			-50	
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			-250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -10\text{ V}, V_{GS} = -10\text{ V}$	-50			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -22\text{ A}$		0.010	0.012	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -19\text{ A}$		0.015	0.018	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -22\text{ A}$		45		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -20\text{ V}, f = 1\text{ MHz}$		5380		μF
Output Capacitance	C_{oss}			570		
Reverse Transfer Capacitance	C_{rss}			500		
Total Gate Charge ^c	Q_g	$V_{DS} = -20\text{ V}, V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		106	159	nC
		$V_{DS} = -20\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		60	90	
Q_{gs}			22			
Q_{gd}			27			
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.4	1.8	3.6	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		15	23	ns
Rise Time ^c	t_r			12	18	
Turn-Off Delay Time ^c	$t_{d(off)}$			70	105	
Fall Time ^c	t_f			18	27	
Drain-Source Body Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}^b$						
Continuous Current	I_S				-60	A
Pulsed Current	I_{SM}				-180	
Forward Voltage ^a	V_{SD}	$I_F = -10\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.5	V
Reverse Recovery Time	t_{rr}	$I_F = -10\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		35	53	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			-2	-3	A
Reverse Recovery Charge	Q_{rr}				33	50

Notes:

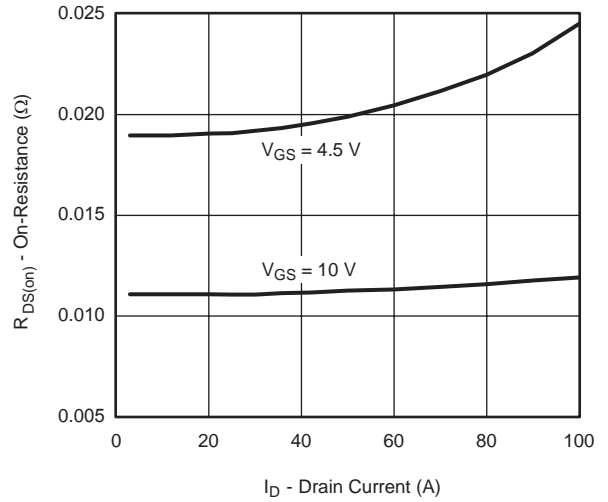
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

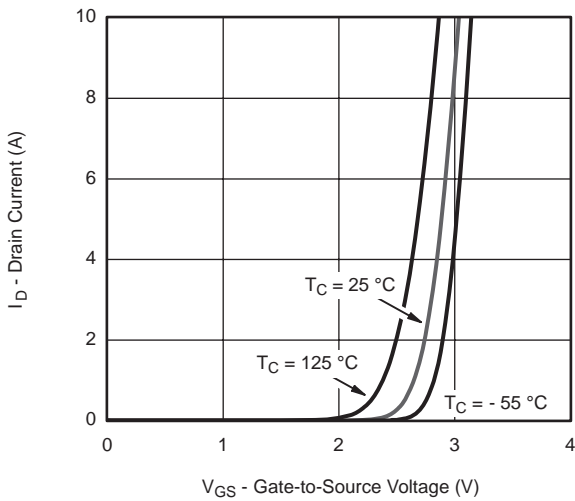
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



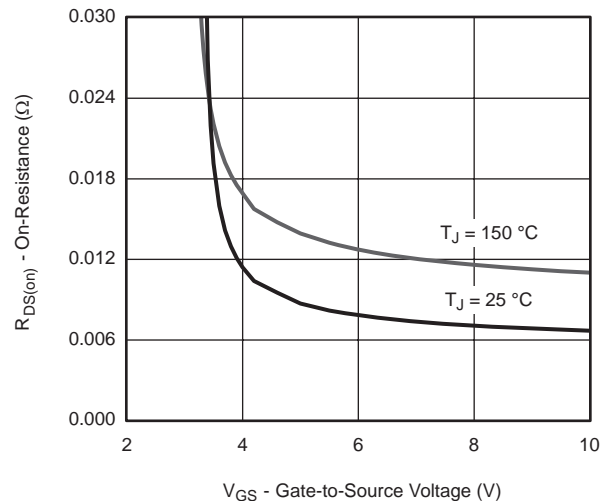
V_{DS} - Drain-to-Source Voltage (V)
Output Characteristics



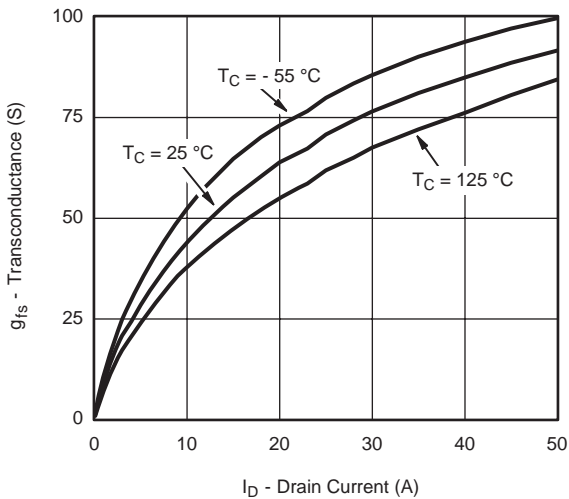
I_D - Drain Current (A)
On-Resistance vs. Drain Current



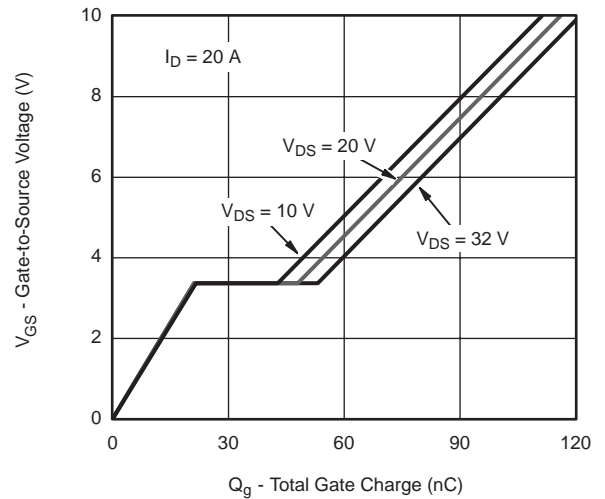
V_{GS} - Gate-to-Source Voltage (V)
Transfer Characteristics



V_{GS} - Gate-to-Source Voltage (V)
On-Resistance vs. Gate-to-Source Voltage

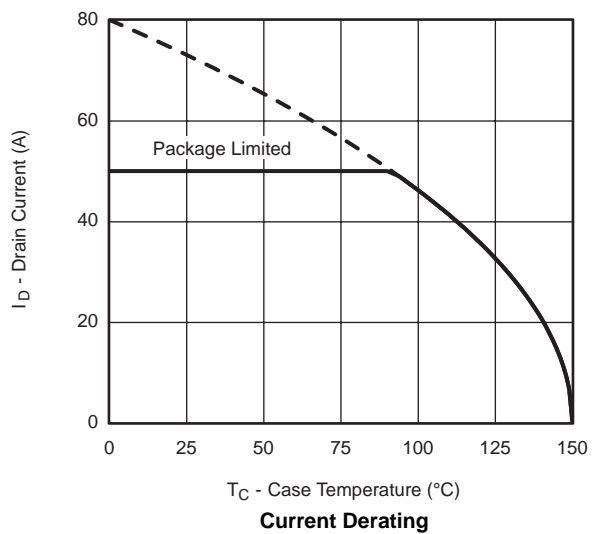
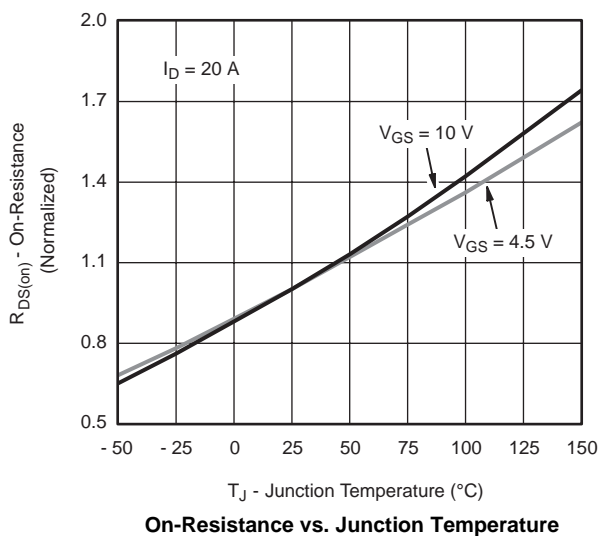
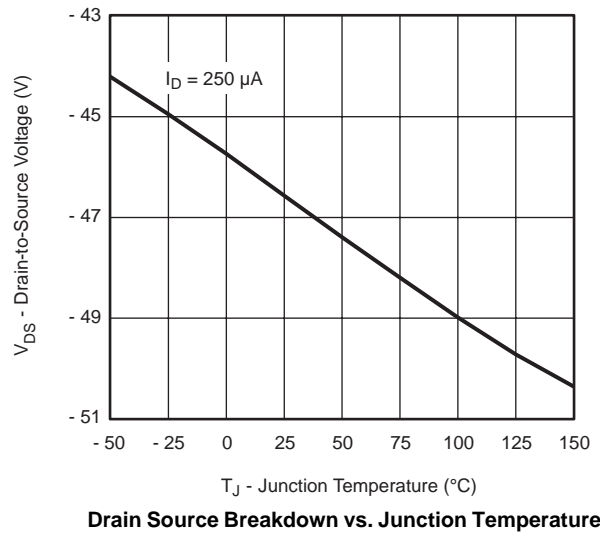
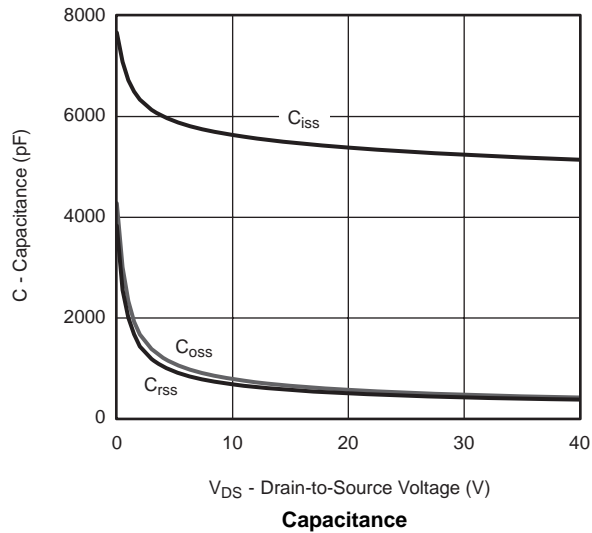
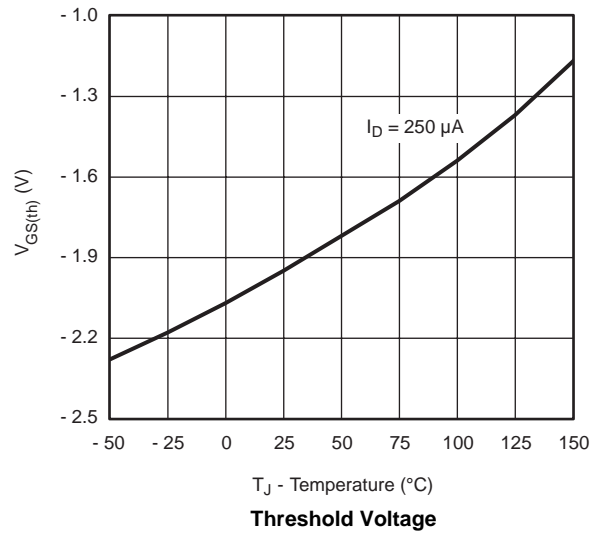
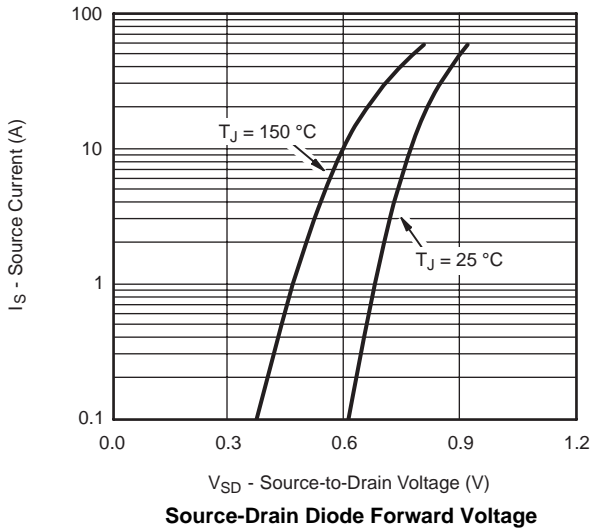


I_D - Drain Current (A)
Transconductance

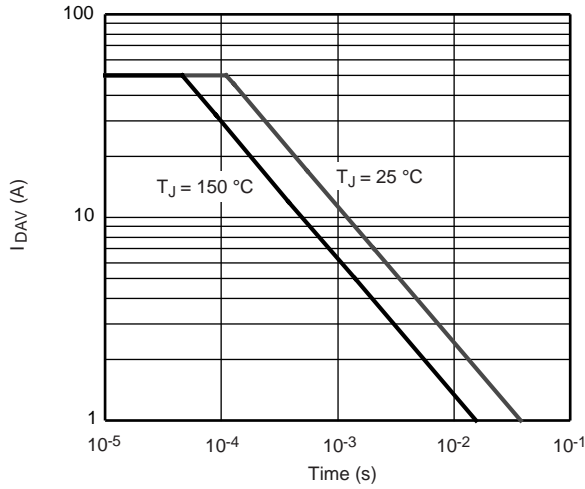


Q_g - Total Gate Charge (nC)
Gate Charge

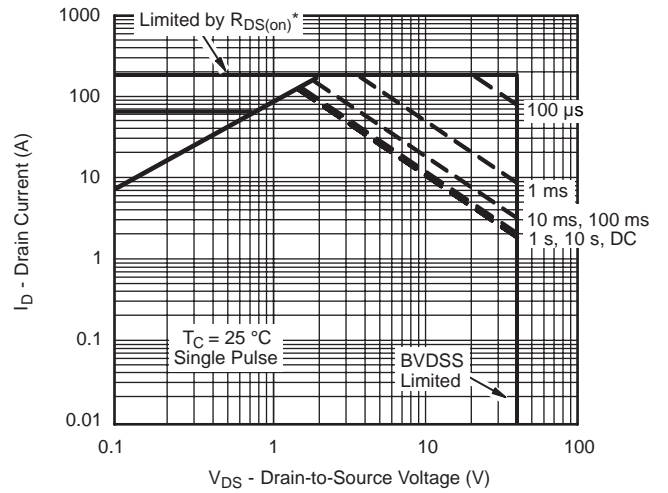
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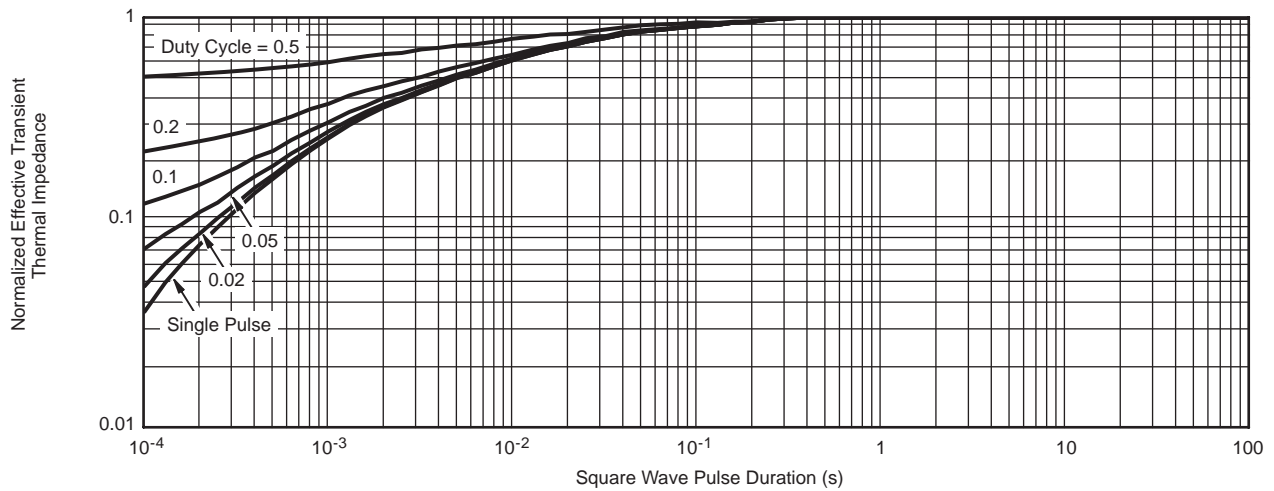


Single Pulse Avalanche Current Capability vs. Time



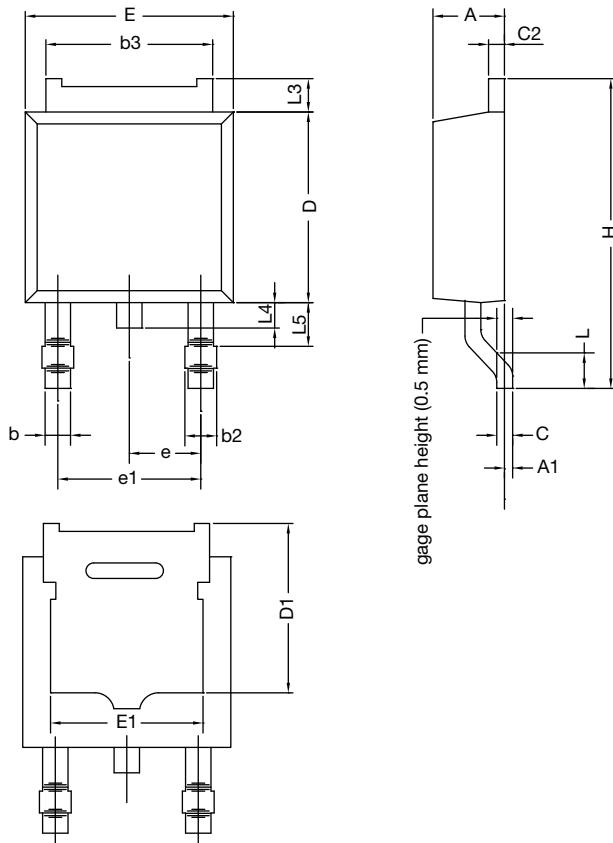
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA CASE OUTLINE

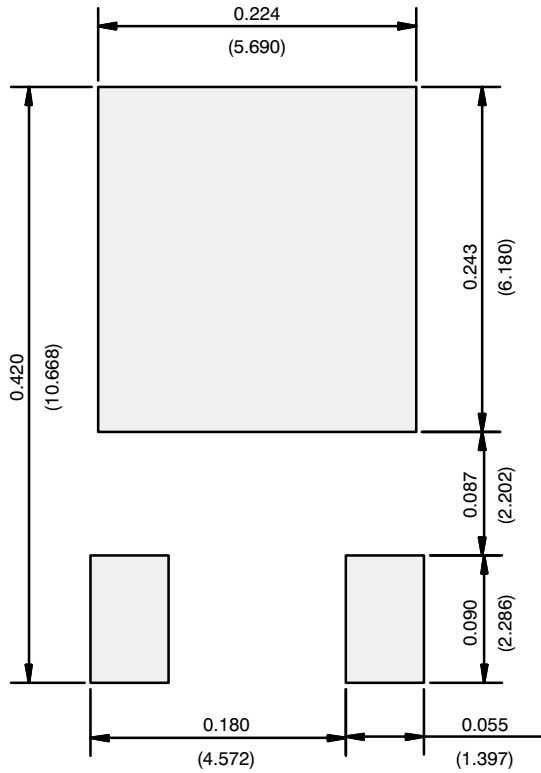


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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